

**FEATURES**

■ **HIGH POWER**

P1dB=42.0dBm at 8.5GHz to 9.6GHz

■ **HIGH GAIN**

G1dB=7.0dB at 8.5GHz to 9.6GHz

■ **BROAD BAND INTERNALLY MATCHED**

■ **HERMETICALLY SEALED PACKAGE**

**RF PERFORMANCE SPECIFICATIONS ( Ta= 25° C )**

CHARACTERISTICS	SYMBOL	CONDITION	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Compression Point	P1dB	VDS= 9V f = 8.5 – 9.6GHz	dBm	41.0	42.0	—
Power Gain at 1dB Compression Point	G1dB		dB	6.0	7.0	—
Drain Current	IDS		A	—	4.5	5.5
Power Added Efficiency	$\eta_{add}$		%	—	31	—
Channel Temperature Rise	$\Delta T_{ch}$	VDS×IDS×Rth(c-c)	°C	—	—	100

**ELECTRICAL CHARACTERISTICS ( Ta= 25° C )**

CHARACTERISTICS	SYMBOL	CONDITION	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 2V IDS= 4.8A	mS	—	3000	—
Pinch-off Voltage	VGSoff	VDS= 2V IDS= 145mA	V	-1.5	-3.0	-4.5
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	A	—	10.0	11.5
Gate-Source Breakdown Voltage	VGSO	IGS= -145 $\mu$ A	V	-5	—	—
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	—	2.0	2.5

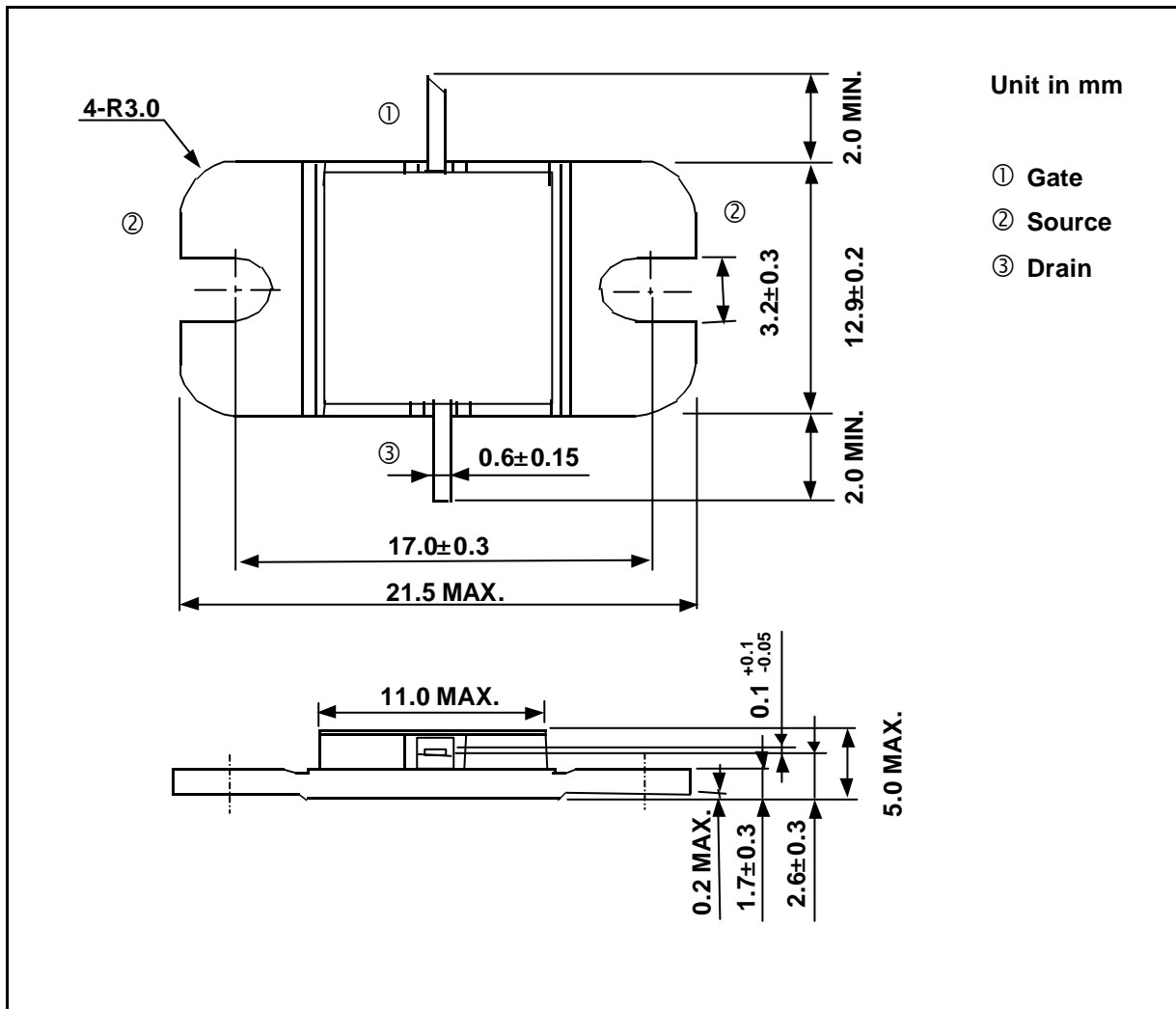
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**ABSOLUTE MAXIMUM RATINGS ( Ta= 25° C )**

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	A	11.5
Total Power Dissipation (Tc= 25 °C)	PT	W	60
Channel Temperature	Tch	°C	175
Storage	Tstg	°C	-65 ~ +175

**PACKAGE OUTLINE (2-11C1B)**



**HANDLING PRECAUTIONS FOR PACKAGED TYPE**

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260° C.